

ABSTRACT OF THE DISCLOSURE

A solid-state imaging device that achieves a reduction in variations appearing on a reproducing screen is provided. The solid-state imaging
5 device includes a plurality of pixel cells that are laid out in matrix form on a semiconductor substrate and a driving unit that is provided to drive the plurality of pixel cells. Each of the plurality of pixel cells includes a photodiode, a MOS transistor, and an element isolating portion 2 that is formed so that the photodiode and the MOS transistor are isolated from
10 each other. The element isolating portion 2 is formed of a STI (Shallow Trench Isolation) that is a grooved portion of the semiconductor substrate. In the semiconductor substrate 7, a STI leakage stopper 1 in which an impurity of a conductive type opposite to a conductive type of source/drain regions in the MOS transistor is introduced is formed to enclose side walls
15 and a bottom face of the element isolating portion 2.